

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Features:

- Non-contact switching
- Fast switching speed
- 0.160" (4.06 mm) wide slot
- 0.300" (7.62 mm) lead spacing
- OPB825R—Optimized for ticket dispensers



Description:

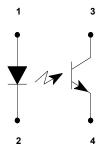
Each OPB825A and OPB825B have an infrared LED, while the OPB825R has a Red LED. All devices have a NPN silicon phototransistor mounted in a low-cost black plastic housing on opposite sides of a 0.160" (4.064 mm) wide slot. OPB825 and OPB825R have no mounting tabs and is intended for direct insertion into PCBoards or dual-in-line sockets. OPB825A has one mounting tab on the phototransistor side, while OPB825B has mounting tabs on both sides (two tabs). Phototransistor switching takes place whenever an opaque object passes through the slot.

Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety
- Ticket Sensing

Ordering Information					
Part Number Description					
OPB825	Slotted Switch (no tabs) IR-LED				
OPB825A	Slotted Switch (one tab) IR-LED				
OPB825B	Slotted Switch (two tabs) IR-LED				
OPB825R	Slotted Switch (no tabs) Red-LED				

Pin#	Description	Pin#	Description
1	Anode	3	Collector
2	Cathode	4	Emitter









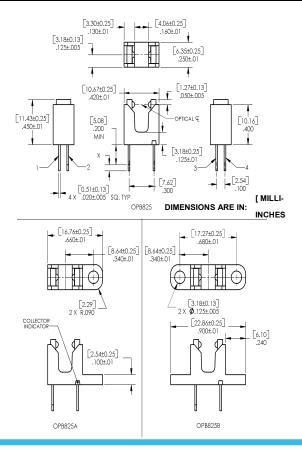
Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage & Operating Temperature Range	-40°C to +85° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾	260° C

Input Diode	OPB825—A—B	OPB825R	
Forward DC Current	50 mA	40 mA	
Peak Forward Current (1 μs pulse width, 300 pps)	3 A	-	
Reverse DC Voltage	2 V	2 V	
Power Dissipation ⁽²⁾	100 mW	100 mW	

Output Phototransistor	OPB825—A—B	OPB825R	
Collector-Emitter Voltage	30 V	24 V	
Emitter-Collector Voltage	5 V	0.4 V	
Collector DC Current	30 mA	30 mA	
Power Dissipation ⁽²⁾	100 mW	100 mW	







OPB825, OPB825A, OPB825B

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	МАХ	UNITS	TEST CONDITIONS	
Input Diode	Input Diode (See OP240 for additional information)						
V _F	Forward Voltage	-	-	1.6	٧	I _F = 20 mA	
I _R	Reverse Current	-	1	100	μΑ	V _R = 2 V	
Output Pho	Output Phototransistor (See OP550 for additional information)						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	1	-	>	I _C = 1 mA	
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	1	-	>	I _E = 100 μA	
I _{CEO}	Collector Dark Current	-	ı	100	nA	$V_{CE} = 10 \text{ V, } I_F = 0, E_E = 0$	
Combined	Combined						
V _{CE(SAT)}	Collector-Emitter Saturation	-	-	0.4	V	I _C = 250 μA, I _F = 20 mA	
I _{C(ON)}	On-State Collector Current	1.0	-	45.0	mA	I _F = 20 mA, V _{CE} = 10 V	

OPB825R

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode	nput Diode (See OVLAS6CB8 for additional information)						
V _F	Forward Voltage	-	2.3	2.6	V	I _F = 20 mA	
I _R	Reverse Current	-	ı	100	μΑ	V _R = 5 V	
Output Pho	Output Phototransistor (See OP750 for additional information)						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	24	1	-	V	$I_E = 100 \mu A, E_E = 0$	
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	0.4	ı	-	٧	$I_E = 100 \mu A, E_E = 0$	
I _{CEO}	Collector Dark Current	-	ı	100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$	
Combined	Combined						
I _{C(OFF)}	OFF-State Collector Current	-	-	0.5	mA	I _F = 0.80 mA, V _{CE} = 5.0 V	
I _{C(ON)}	On-State Collector Current	2.5	-	16.0	mA	I _F = 8.00 mA, V _{CE} = 0.5 V	

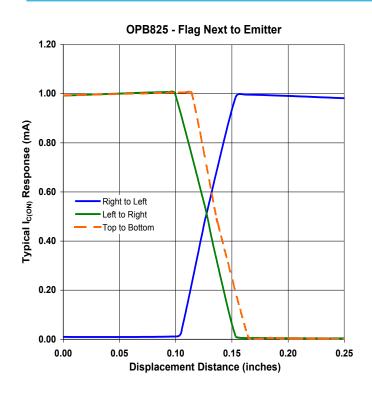
Notes:

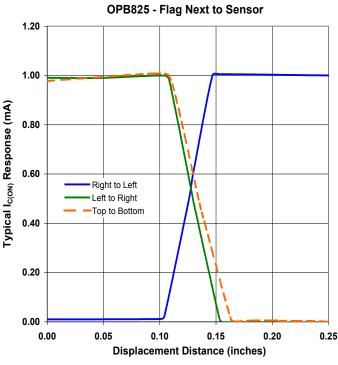
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25 °C.
- (3) All parameters tested using pulse techniques.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.
- (5) Simulates optical path blocked with thick paper

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OPB825 - Flag Next to Emitter 1.20 1.00 Typical I_{C(ON)} Response (mA) 0.80 0.60 Right to Left Left to Right -Top to Bottom 0.20 0.00 0.05 0.20 0.25 0.00 0.10 0.15 **Displacement Distance (inches)**

Mech. Q -←0→+ IR Opaque Object Detector

Test Schematic

General Note